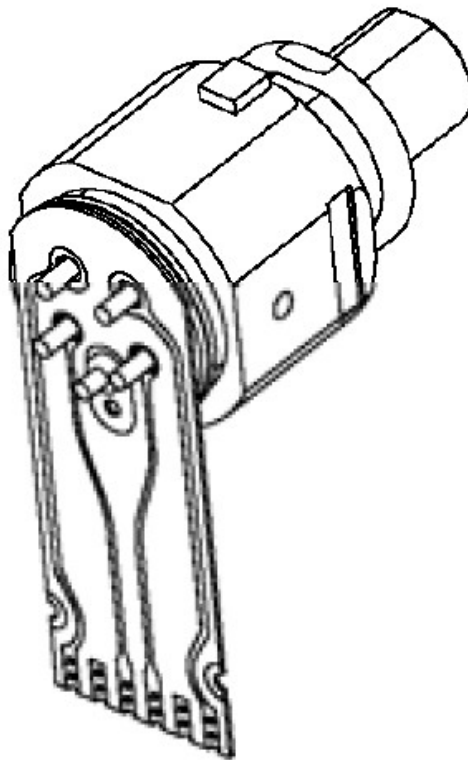


Lc-TOSA 850nm 10G



KEY FEATURE

- Operate to 10 Gbps NRZ rates
- Differential driven
- Low electrical parasitic TO package
- Package with flex cable or without flex cable is available

APPLICATIONS

- 10GBASE-SR
- 8XFC

LC-TOSA 850nm 10G

SPECIFICATIONS

Absolute maximum ratings:

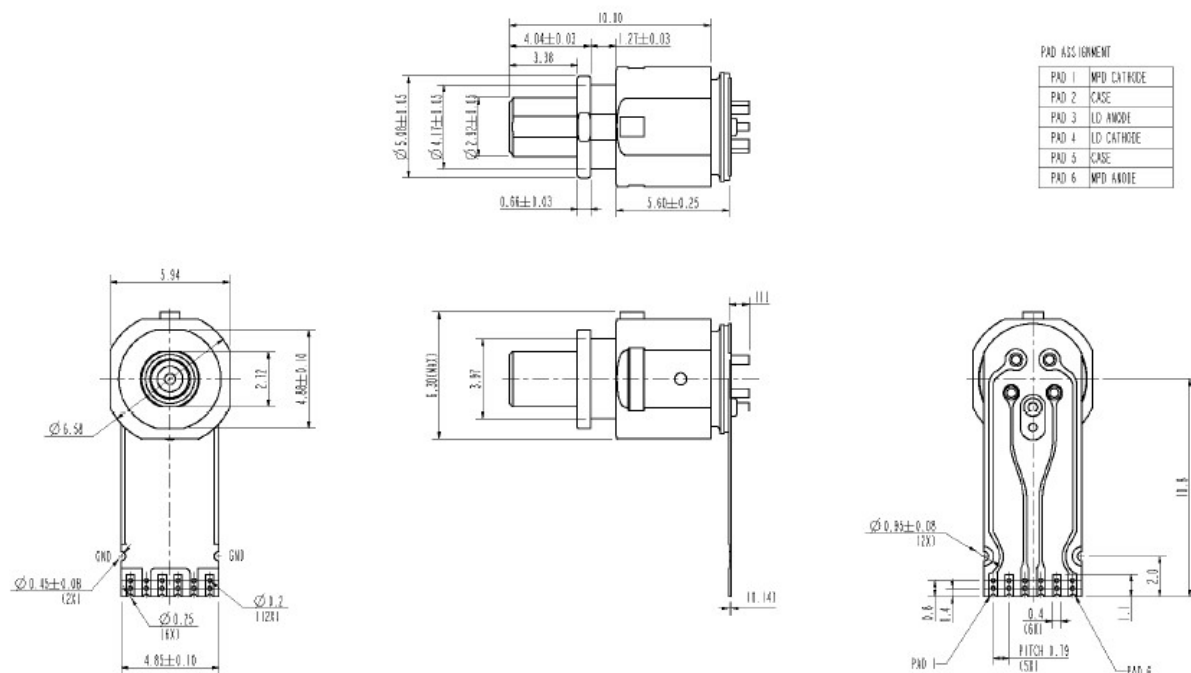
Parameter	Rating
Storage Temperature	-40°C ~ +85°C
Operating Temperature	-5°C ~ +75°C
Soldering Process Temperature	260°C, 10 second

Electro-optical Characteristics (Unless otherwise specified, $T_A = 25^\circ\text{C}$):

VCSEL Parameter	Symbol	Unit	Min	Typ.	Max	Conditions
Peak Wavelength	λ_P	nm	840	850	860	$I_{op} = 6\text{mA}$;
λ_P Temperature variation	$\Delta\lambda_P / \Delta T$	nm/K		0.07		
RMS spectrum Bandwidth	$\Delta\lambda$	nm			0.45	$I_{op} = 6\text{mA}$;
Threshold Current	I_{th}	mA	0.3	0.8	1.6	$T = -5\sim+75^\circ\text{C}$
Rise time / Fall time	T_R/T_F	ps		30/45	55	$I_{op} = 6\text{mA}$; ER = 5dB; (20 – 80%)
Laser Forward Voltage	V_F	V	1.6	2.0	2.4	$I_{op} = 6\text{mA}$; $T = -5\sim+75^\circ\text{C}$
Slope Efficiency	η	W/A	0.06	0.13	0.2	$T = -5\sim+75^\circ\text{C}$
Slope efficiency temperature variation	$\Delta\eta / \Delta T$	%/°C		-0.6		
Effective Circuit Resistance	R_S	Ω	70	85	100	
Dark Current	I_{dark}	nA			20	$V_R = 2\text{V}$
Monitor Diode Current	I_{PD}	μA	200	500	900	$P_{OC} = 0.5\text{mW}$
Relative Intensity Noise	RIN	dB/Hz		-130	-120	
Tracking error	T/E	-1.0		1.0	dB	Fixed Power=0.5mW $T_A = -5^\circ\text{C}$ to $+75^\circ\text{C}$

Lc-TOSA 850nm 10G

PRODUCT DRAWING



PART NUMBER

8090014703

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